

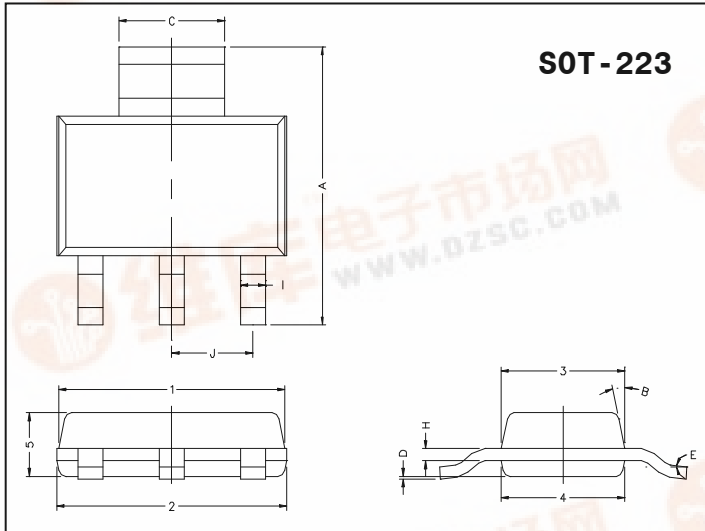
GTM CORPORATION

GLA27 NPN TRANSISTOR

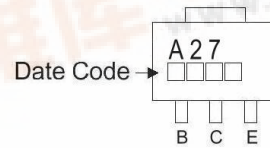
Description

The GLA27 is designed for darlington amplifier high current gain collector current to 500mA.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13 TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

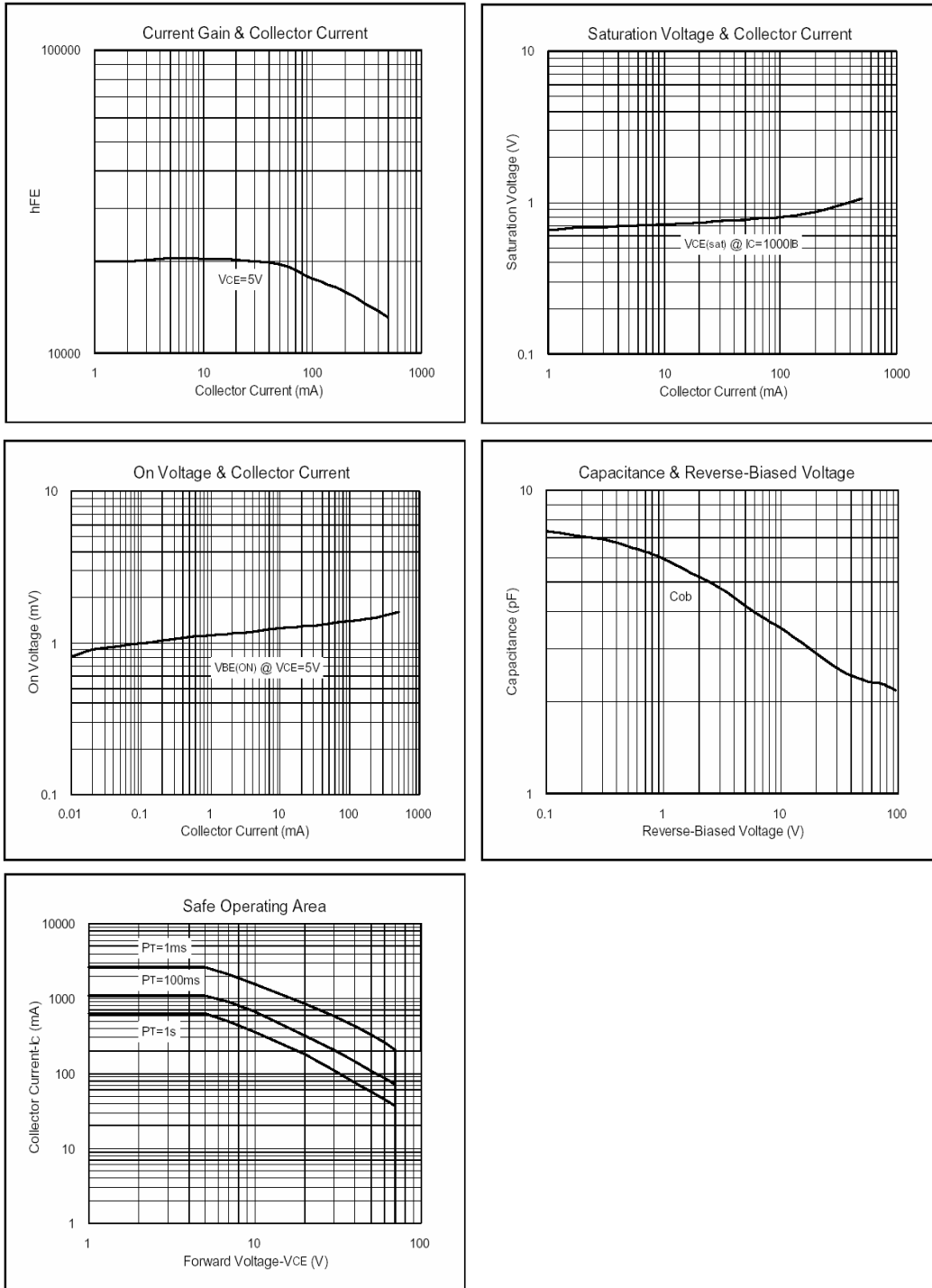
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	60	V
Collector to Emitter Voltage	VCES	60	V
Emitter to Base Voltage	VEBO	10	V
Collector Current	IC	500	mA
Total Power Dissipation	PD	2	W

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=100uA, IE=0
BVCES	60	-	-	V	IC=100uA, VBE=0
BVEBO	10	-	-	V	IE=10uA, IC=0
ICBO	-	-	100	nA	VCB=50V, IE=0
IEBO	-	-	100	nA	VEB=10V, IC=0
ICES	-	-	500	nA	VCE=50V
VCE(sat)	-	-	1.5	V	IC=100mA, IB=0.1mA
VBE(sat)	-	-	2.0	V	IC=100mA, VCE=5V
hFE1	10K	-	-		VCE=5V, IC=10mA
hFE2	10K	-	-		VCE=5V, IC=100mA

Characteristics Curve



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